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# FDN358P

# Single P-Channel, Logic Level, PowerTrench® MOSFET

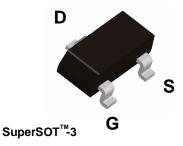
### **General Description**

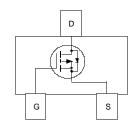
This P-Channel Logic Level MOSFET is produced using Fairchild Semiconductor advanced Power Trench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

These devices are well suited for portable electronics applications: load switching and power management, battery charging circuits, and DC/DC conversion.

#### **Features**

- -1.5 A, -30 V.  $R_{DS(ON)} = 125 \text{ m}\Omega$  @  $V_{GS} = -10 \text{ V}$   $R_{DS(ON)} = 200 \text{ m}\Omega$  @  $V_{GS} = -4.5 \text{ V}$
- Low gate charge (4 nC typical)
- $\bullet \;\; \mbox{High performance trench technology for extremely} \;\; \mbox{low} \;\; \mbox{R}_{\mbox{\scriptsize DS(ON)}} \; .$
- High power version of industry Standard SOT-23 package. Identical pin-out to SOT-23 with 30% higher power handling capability.





### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		-30	V
V <sub>GSS</sub>	Gate-Source Voltage		±20	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	-1.5	A
	- Pulsed		<b>-</b> 5	
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1a)	0.5	W
		(Note 1b)	0.46	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C

### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
R <sub>e,JC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

**Package Marking and Ordering Information** 

Device Marking	Device	Reel Size	Tape width	Quantity
358	FDN358P	7"	8mm	3000 units

# **Electrical Characteristics**

T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	1		l	l	ı
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-30			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$ , Referenced to 25°C		-22		mV/°C
1	Zoro Cata Valtago Drain Current	$V_{DS} = -24V$ , $V_{GS} = 0 V$			-1	μΑ
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -24V$ , $V_{GS} = 0$ V, $T_J = 55$ °C			-10	
I <sub>GSSF</sub>	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V},  V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1	-1.9	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$ , Referenced to 25°C		4		mV/°C
R <sub>DS(on)</sub>	Static Drain-Source	$V_{GS} = -10 \text{ V}, \qquad I_{D} = -1.5 \text{ A}$		105	125	mΩ
	On–Resistance	$V_{GS} = -10 \text{ V}, I_D = -1.5 \text{ A}, T_J = 125^{\circ}\text{C}$		148	210	
		$V_{GS} = -4.5 \text{ V}, \qquad I_D = -1.2 \text{A},$		161	200	
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-5			Α
<b>g</b> <sub>FS</sub>	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -1.5 \text{ A}$		3.5		S
Dynamic	Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -15 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		182		pF
Coss	Output Capacitance	f = 1.0 MHz		56		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			26		pF
Switchir	ng Characteristics (Note 2)			•	•	
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = -15 \text{ V}, \qquad I_D = -0.5 \text{ A},$		5	10	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = -15 \text{ V}, \qquad I_{D} = -0.5 \text{ A}, \\ V_{GS} = -10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		13	23	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			12	21	ns
t <sub>f</sub>	Turn-Off Fall Time			2	4	ns
$\overline{Q_g}$	Total Gate Charge	$V_{DS} = -15V$ , $I_{D} = -1.5 A$ ,		4	5.6	nC
$\overline{Q_{gs}}$	Gate-Source Charge	$V_{GS} = -10 \text{ V}$		0.8		nC
Q <sub>gd</sub>	Gate-Drain Charge	1		0.8		nC
	ource Diode Characteristics	and Maximum Ratings		•	•	
I <sub>s</sub>	Maximum Continuous Drain–Source				-0.42	Α
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V},  I_S = -0.42 \text{ A (Note 2)}$		-0.76	-1.2	V

#### Notes

 R<sub>QUA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>QUC</sub> is guaranteed by design while R<sub>QCA</sub> is determined by the user's board design.



a) 250°C/W when mounted on a 0.02 in² pad of 2 oz. copper.



b) 270°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $\leq\!300~\mu\text{s},$  Duty Cycle  $\leq\!2.0\%$ 

# **Typical Characteristics**

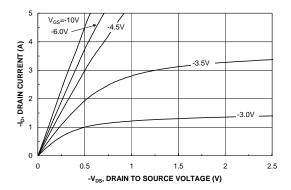


Figure 1. On-Region Characteristics.

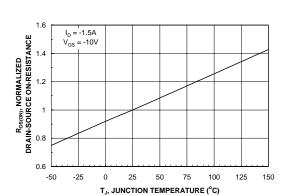


Figure 3. On-Resistance Variation with Temperature.

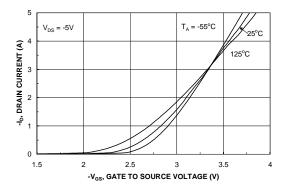


Figure 5. Transfer Characteristics.

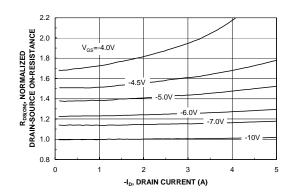


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

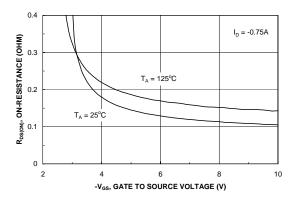


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

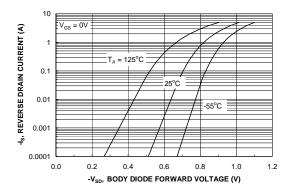
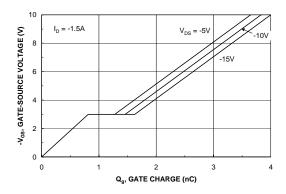


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# **Typical Characteristics**



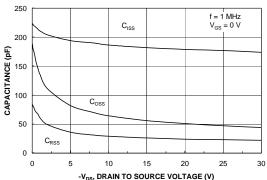
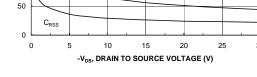


Figure 7. Gate Charge Characteristics.



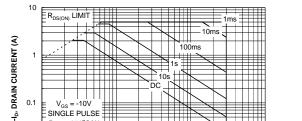


Figure 8. Capacitance Characteristics.

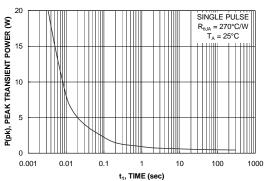


Figure 9. Maximum Safe Operating Area.

-V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)

0.1

0.01

0.1

10V SINGLE PULSE

 $R_{\theta JA} = 270^{\circ} C/W$  $T_A = 25^{\circ}C$ 



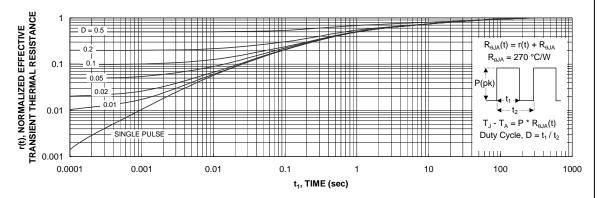


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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